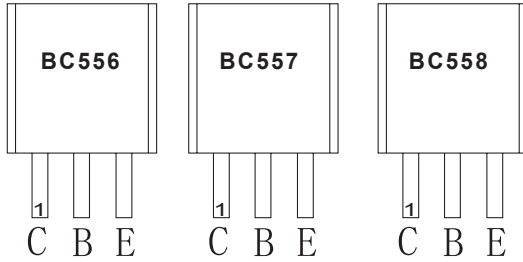


BC556 / BC557 / BC558 TRANSISTOR (PNP)

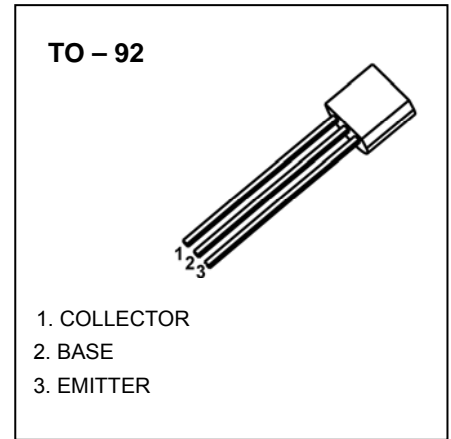
FEATURES

- High Voltage
- Complement to BC546,BC547,BC548

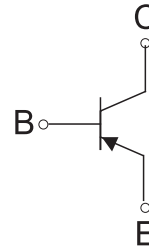
MARKING



BC556,BC557,BC558=Device code
 Solid dot=Green molding compound device,
 if none,the normal device



Equivalent Circuit



MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	BC556	-80
		BC557	-50
		BC558	-30
V _{CEO}	Collector-Emitter Voltage	BC556	-65
		BC557	-45
		BC558	-30
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current-Continuous	-0.1	A
P _C	Collector Power Dissipation	625	mW
R _{θJA}	Thermal Resistance from Junction to Ambient	200	°C/W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~+150	°C

PACKING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
BC556	TO-92	Bulk	1000pcs/Bag
BC556-T	TO-92	Tape	2000pcs/Box
BC557	TO-92	Bulk	1000pcs/Bag
BC557-T	TO-92	Tape	2000pcs/Box
BC558	TO-92	Bulk	1000pcs/Bag
BC558-T	TO-92	Tape	2000pcs/Box

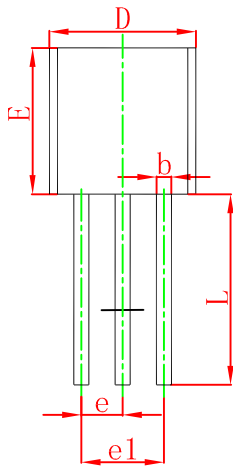
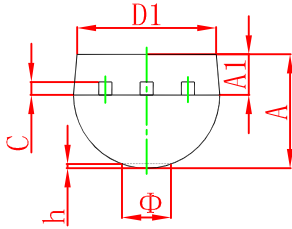
ELECTRICAL CHARACTERISTICS
 $T_a = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit	
Collector-base breakdown voltage	BC556	$I_C = -0.1\text{mA}, I_E = 0$	-80			V	
	BC557		-50				
	BC558		-30				
Collector-emitter breakdown voltage	BC556	$I_C = -2\text{mA}, I_B = 0$	-65			V	
	BC557		-45				
	BC558		-30				
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu\text{A}, I_C = 0$	-5			V	
Collector cut-off current	BC556	I_{CBO}	$V_{CB} = -70\text{V}, I_E = 0$		-0.1	μA	
	BC557		$V_{CB} = -45\text{V}, I_E = 0$		-0.1	μA	
	BC558		$V_{CB} = -25\text{V}, I_E = 0$		-0.1	μA	
Collector cut-off current	BC556	I_{CEO}	$V_{CE} = -60\text{V}, I_B = 0$		-0.1	μA	
	BC557		$V_{CE} = -40\text{V}, I_B = 0$		-0.1	μA	
	BC558		$V_{CE} = -25\text{V}, I_B = 0$		-0.1	μA	
Emitter cut-off current	I_{EBO}	$V_{EB} = -5\text{V}, I_C = 0$			-0.1	μA	
DC current gain	h_{FE}^*	$V_{CE} = -5\text{V}, I_C = -2\text{mA}$	120		800		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10\text{mA}, I_B = -0.5\text{mA}$			-0.3	V	
		$I_C = -100\text{mA}, I_B = -5\text{mA}$			-0.65	V	
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -10\text{mA}, I_B = -0.5\text{mA}$			-0.8	V	
		$I_C = -100\text{mA}, I_B = -5\text{mA}$			-1	V	
Base-emitter voltage	V_{BE}	$V_{CE} = -5\text{V}, I_C = -2\text{mA}$	-0.55		-0.7	V	
		$V_{CE} = -5\text{V}, I_C = -10\text{mA}$			-0.82	V	
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$			6	pF	
Transition frequency	BC556	f_T	$V_{CE} = -5\text{V}, I_C = -10\text{mA}, f = 100\text{MHz}$		150		MHz
	BC557				150		MHz
	BC558				150		MHz

CLASSIFICATION of h_{FE}

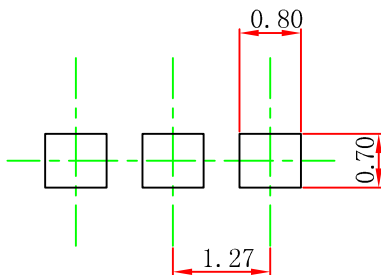
RANK	A	B	C
RANGE	120-220	180-460	420-800

TO-92 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	3.300	3.700	0.130	0.146
A1	1.100	1.400	0.043	0.055
b	0.380	0.550	0.015	0.022
c	0.360	0.510	0.014	0.020
D	4.300	4.700	0.169	0.185
D1	3.430		0.135	
E	4.300	4.700	0.169	0.185
e	1.270 TYP		0.050 TYP	
e1	2.440	2.640	0.096	0.104
L	14.100	14.500	0.555	0.571
Φ		1.600		0.063
h	0.000	0.380	0.000	0.015

TO-92 Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.